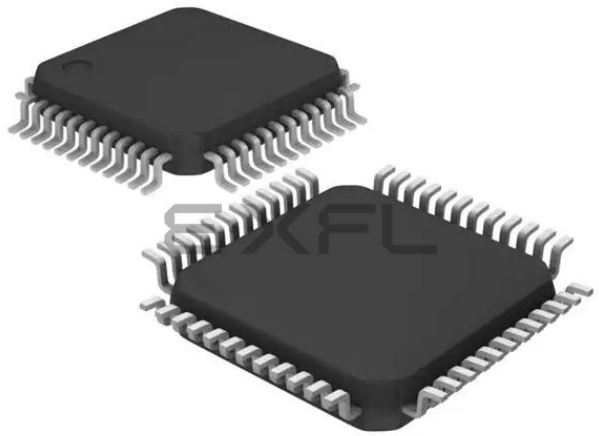

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	40MHz
Connectivity	I²C, LINbus, SCI, SPI
Peripherals	LCD, LVD, POR, PWM, WDT
Number of I/O	39
Program Memory Size	18KB (18K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1.9K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 9x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/s9s08lg16j0vlf

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Table 1. MC9S08LG32 Series Features by MCU and Package

Feature	MC9S08LG32			MC9S08LG16	
Flash size (bytes)	32,768			18,432	
RAM size (bytes)	1984				
Pin quantity	80	64	48	64	48
ADC	16 ch	12 ch	9 ch	12 ch	9 ch
LCD	8 x 37 4 x 41	8 x 29 4 x 33	8 x 21 4 x 25	8 x 29 4 x 33	8 x 21 4 x 25
ICE + DBG	yes				
ICS	yes				
IIC	yes				
IRQ	yes				
KBI	8 pin				
GPIOs	69	53	39	53	39
RTC	yes				
MTIM	yes				
SCI1	yes				
SCI2	yes				
SPI	yes				
TPM1 channels	2				
TPM2 channels	6				
XOSC	yes				

1 Pin Assignments

This section shows the pin assignments for the MC9S08LG32 series devices. The priority of functions on a pin is in ascending order from left to right and bottom to top. Another view of pinouts and function priority is given in Table 2.

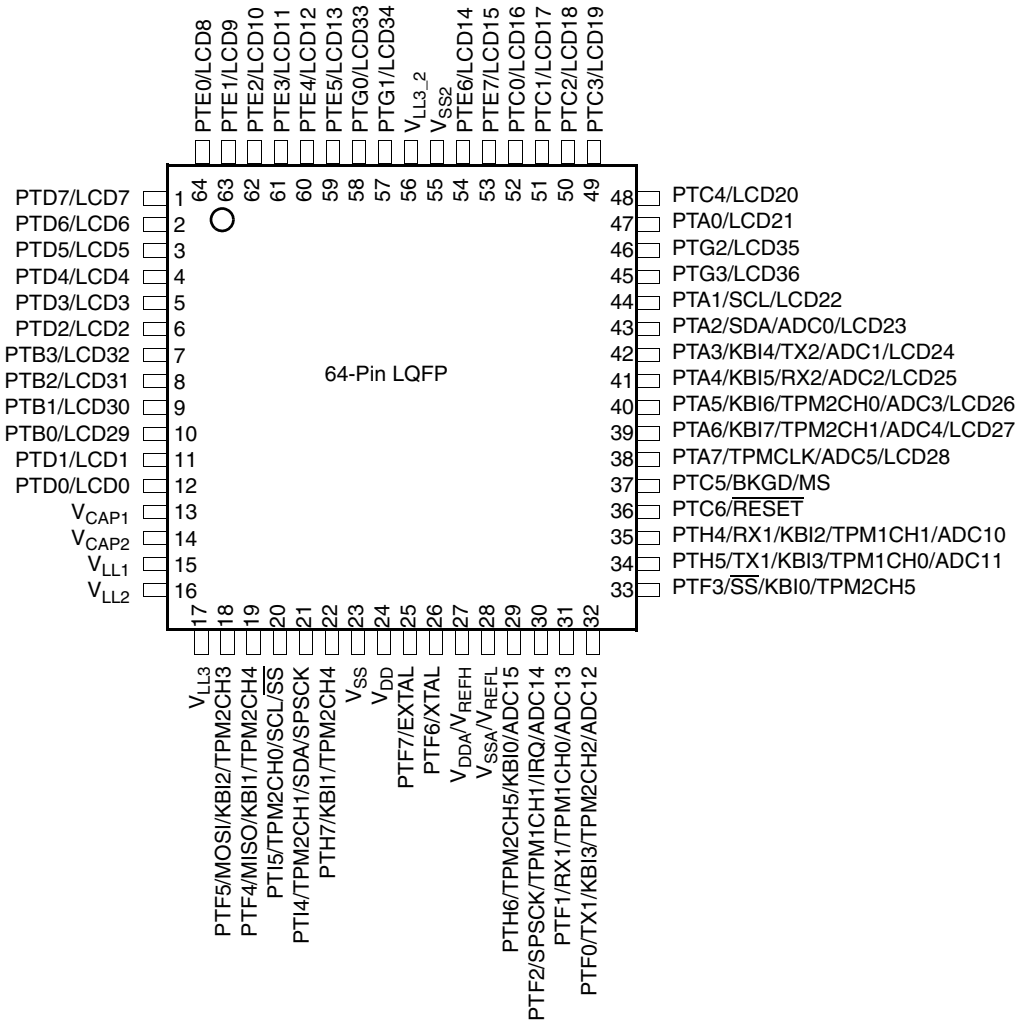


Figure 3. 64-Pin LQFP

NOTE

V_{REFH}/V_{REFL} are internally connected to V_{DDA}/V_{SSA}.

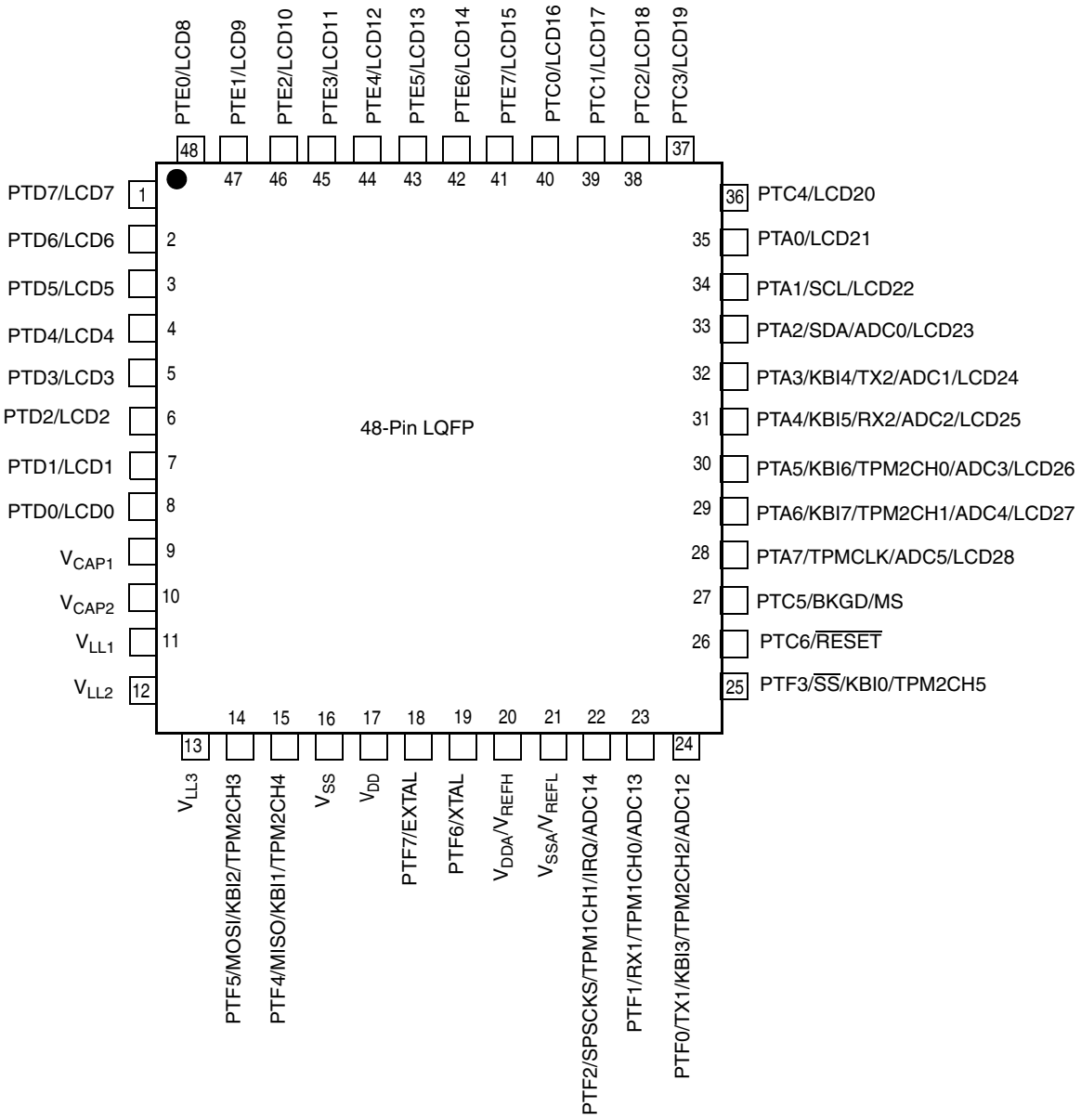


Figure 4. 48-Pin LQFP

NOTE

V_{REFH}/V_{REFL} are internally connected to V_{DDA}/V_{SSA}.

Table 2. Pin Availability by Package Pin-Count (continued)

Packages			<-- Lowest **Priority** --> Highest				
80	**64**	**48**	**Port Pin**	**Alt 1**	**Alt 2**	**Alt 3**	**Alt 4**
39	31	23	PTF1	RX1	TPM1CH0	ADC13	—
40	32	24	PTF0	TX1	KBI3	TPM2CH2	ADC12
41	33	25	PTF3	$\overline{SS}$	KBI0	TPM2CH5	—
42	34	—	PTH5	TX1	KBI3	TPM1CH0	ADC11
43	35	—	PTH4	RX1	KBI2	TPM1CH1	ADC10
44	—	—	PTH3	KBI7	ADC9	—	—
45	—	—	PTH2	KBI6	ADC8	—	—
46	—	—	PTH1	KBI5	ADC7	—	—
47	—	—	PTH0	KBI4	ADC6	—	—
48	36	26	PTC6	$\overline{RESET}$	—	—	—
49	37	27	PTC5	BKGD/MS	—	—	—
50	38	28	PTA7	TPMCLK	ADC5	LCD28	—
51	39	29	PTA6	KBI7	TPM2CH1	ADC4	LCD27
52	40	30	PTA5	KBI6	TPM2CH0	ADC3	LCD26
53	41	31	PTA4	KBI5	RX2	ADC2	LCD25
54	42	32	PTA3	KBI4	TX2	ADC1	LCD24
55	43	33	PTA2	SDA	ADC0	LCD23	—
56	44	34	PTA1	SCL	LCD22	—	—
57	45	—	PTG3	LCD36	—	—	—
58	46	—	PTG2	LCD35	—	—	—
59	47	35	PTA0	LCD21	—	—	—
60	48	36	PTC4	LCD20	—	—	—
61	49	37	PTC3	LCD19	—	—	—
62	50	38	PTC2	LCD18	—	—	—
63	51	39	PTC1	LCD17	—	—	—
64	52	40	PTC0	LCD16	—	—	—
65	53	41	PTE7	LCD15	—	—	—
66	54	42	PTE6	LCD14	—	—	—
67	55	—	V_{SS2}	—	—	—	—
68	56	—	V_{LL3_2}	—	—	—	—
69	—	—	PTG7	LCD44	—	—	—
70	—	—	PTG6	LCD43	—	—	—
71	—	—	PTG5	LCD42	—	—	—
72	—	—	PTG4	LCD41	—	—	—
73	57	—	PTG1	LCD34	—	—	—
74	58	—	PTG0	LCD33	—	—	—
75	59	43	PTE5	LCD13	—	—	—
76	60	44	PTE4	LCD12	—	—	—

Table 2. Pin Availability by Package Pin-Count (continued)

Packages			<-- Lowest **Priority** --> Highest				
80	**64**	**48**	**Port Pin**	**Alt 1**	**Alt 2**	**Alt 3**	**Alt 4**
77	61	45	PTE3	LCD11	—	—	—
78	62	46	PTE2	LCD10	—	—	—
79	63	47	PTE1	LCD9	—	—	—
80	64	48	PTE0	LCD8	—	—	—

2 Electrical Characteristics

2.1 Introduction

This section contains electrical and timing specifications for the MC9S08LG32 series of microcontrollers available at the time of publication.

2.2 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 3. Parameter Classifications

P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled “C” in the parameter tables where appropriate.

2.3 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 4 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

This device contains circuitry that protects against damage due to high static voltage or electrical fields. However, it is advised that normal precautions should be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}) or the programmable pull-up resistor associated with the pin is enabled.

Table 4. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	–0.3 to +5.8	V
Maximum current into V_{DD}	I_{DD}	120	mA
Digital input voltage	V_{In}	–0.3 to V_{DD} + 0.3	V
Instantaneous maximum current Single pin limit (applies to all port pins)[1, 2, 3]	I_D	±25 ±2	mA
Storage temperature range	T_{stg}	–55 to 150	°C

1 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages and use the largest of the two resistance values.

2 All functional non-supply pins are internally clamped to V_{SS} and V_{DD}.

3 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in an external power supply going out of regulation. Ensure that the external V_{DD} load will shunt current greater than maximum injection current, this will be of greater risk when the MCU is not consuming power. For instance, if no system clock is present, or if the clock rate is very low (which would reduce overall power consumption).

2.4 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in On-Chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 5. Thermal Characteristics

Rating	Symbol	Value	Unit
Operating temperature range (packaged)	T_A	T_L to T_H –40 to +105	°C
Maximum junction temperature	T_J	125	°C
Thermal resistance Single-layer board 80-pin LQFP 64-pin LQFP 48-pin LQFP	θ_{JA}	 61 71 80	°C/W
Thermal resistance Four-layer board 80-pin LQFP 64-pin LQFP 48-pin LQFP	θ_{JA}	 48 52 56	°C/W

The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_J = T_A + (P_D \times \theta_{JA}) \qquad \textit{Eqn. 1}$$

where:

T_A = Ambient temperature, °C
θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W
$P_D = P_{int} + P_{I/O}$
$P_{int} = I_{DD} \times V_{DD}$, Watts — chip internal power
$P_{I/O}$ = Power dissipation on input and output pins — user determined

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273\ °C) \qquad \textit{Eqn. 2}$$

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273\ °C) + \theta_{JA} \times (P_D)^2 \qquad \textit{Eqn. 3}$$

where K is a constant pertaining to the particular part. K can be determined from equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving Equation 1 and Equation 2 iteratively for any value of T_A.

2.5 ESD Protection and Latch-Up Immunity

Although damage from electrostatic discharge (ESD) is much less common on these devices than on early CMOS circuits, normal handling precautions should be taken to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with AEC-Q100 Stress Test Qualification for automotive grade integrated circuits. During the device qualification, ESD stresses were performed for the human body model (HBM), the machine model (MM) and the charge device model (CDM).

A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless instructed otherwise in the device specification.

Table 6. ESD and Latch-Up Test Conditions

Model	Description	Symbol	Value	Unit
Human Body Model	Series resistance	R1	1500	Ω
	Storage capacitance	C	100	pF
	Number of pulses per pin	—	3	—
Latch-up	Minimum input voltage limit	—	–2.5	V
	Maximum input voltage limit	—	7.5	V

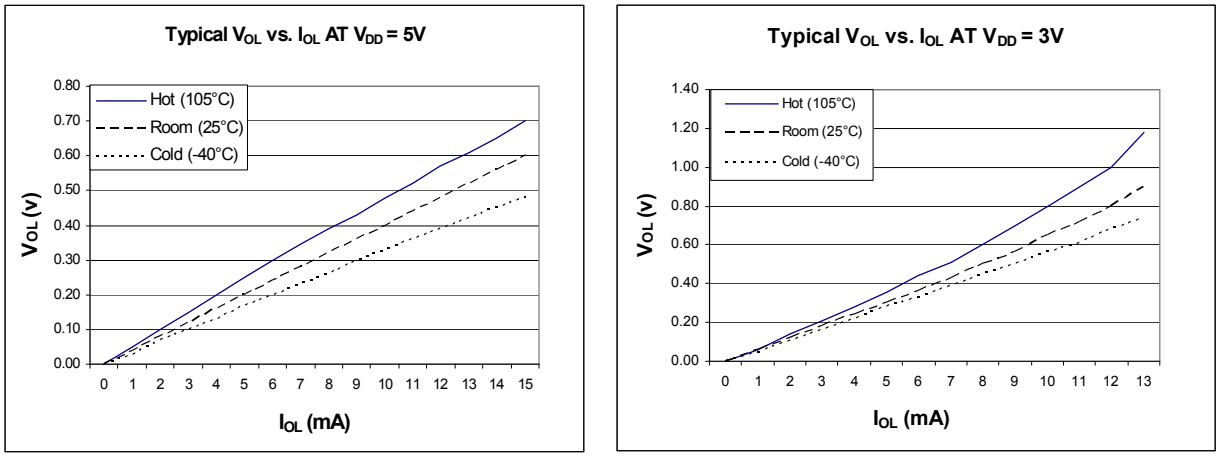


Figure 5. Typical Low-side Drive (sink) characteristics – High Drive (PTxDSn = 1)

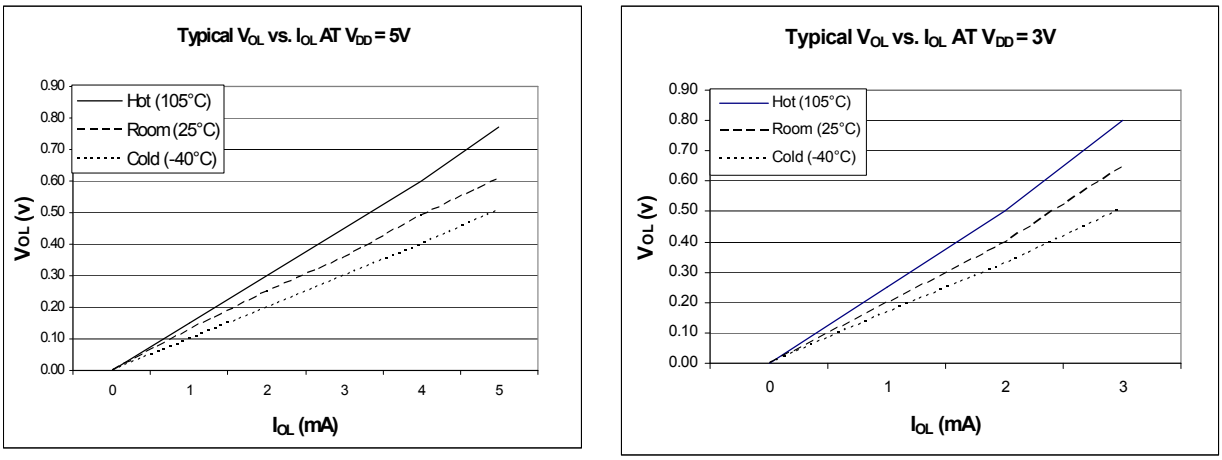


Figure 6. Typical Low-side Drive (sink) characteristics – Low Drive (PTxDSn = 0)

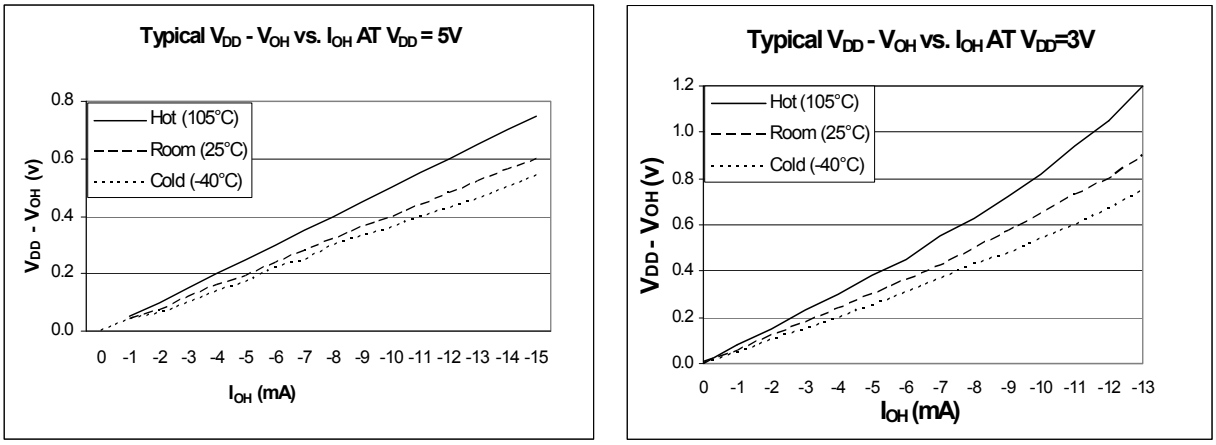


Figure 7. Typical High-side Drive (source) characteristics – High Drive (PTxDSn = 1)

Table 9. Supply Current Characteristics (continued)

Num	C	Parameter		Symbol	Bus Freq	V_{DD} (V)	Typ[1]	Max	Unit	Temp (°C)
6	T	Stop2 adders:	RTC using LPO	—	n/a	3	210	—	nA	–40 °C to 105 °C
			RTC using low power crystal oscillator				4.25	—	µA	
			LCD[2] with rbias (Low Gain)				1.2[3]	—		
			LCD[2] with rbias (High Gain)				18[4]	—		
			LCD[2] with Cpump				4.05[3]	—		–40 °C to 85 °C
			RTC using LPO			5	210	—	nA	–40 °C to 105 °C
			RTC using low power crystal oscillator				4.22	—	µA	
			LCD[2] with rbias (Low Gain)				1.5[3]	—		
			LCD[2] with rbias (High Gain)				32[4]	—		
			LCD[2] with Cpump				7.12[3]	—		–40 °C to 85 °C
7	T	Stop3 adders:	RTC using LPO	—	n/a	3	210	—	nA	–40 °C to 105 °C
			RTC using low power crystal oscillator				4.75	—	µA	
			LCD[2] with rbias (Low Gain)				1.2[3]	—		
			LCD[2] with rbias (High Gain)				18[4]	—		
			LCD[2] with Cpump				4.35[3]	—		–40 °C to 85 °C
			RTC using LPO			5	230	—	nA	–40 °C to 105 °C
			RTC using low power crystal oscillator				4.74	—	µA	
			LCD[2] with rbias (Low Gain)				1.5[3]	—		
			LCD[2] with rbias (High Gain)				32[4]	—		
			LCD[2] with Cpump				7.49[3]	—		–40 °C to 85 °C

Table 9. Supply Current Characteristics (continued)

Num	C	Parameter		Symbol	Bus Freq	V_{DD} (V)	Typ[1]	Max	Unit	Temp (°C)
8	T	Stop3 adders:	EREFSTEN = 1	—	n/a	3	4.58	—	µA	–40 °C to 105 °C
			IREFSTEN = 1				71.7	—		
			LVD				94.35	—		
			EREFSTEN = 1			5	4.61	—	µA	
			IREFSTEN = 1				71.69	—		
			LVD				107.34	—		

1 Typical values are measured at 25 °C. Characterized, not tested.

2 LCD configured for Charge Pump Enabled V_{LL3} connected to V_{DD}.

3 This does not include current required for 32 kHz oscillator.

4 This is the maximum current when all LCD inputs/outputs are used.

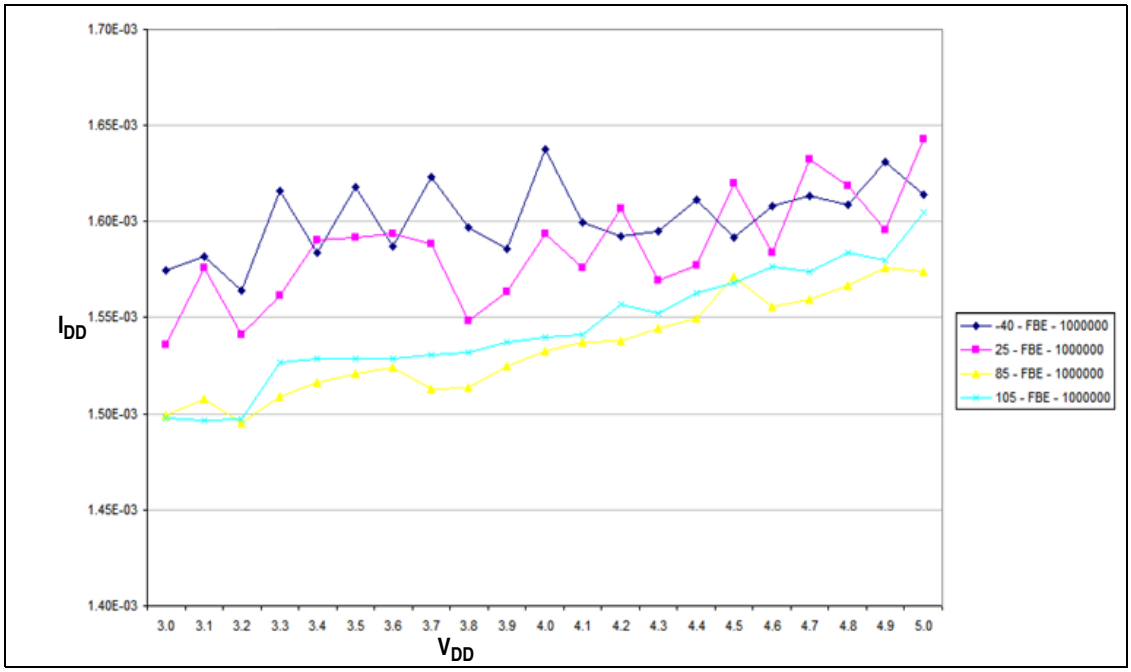


Figure 9. Typical Run I_{DD} for FBE Mode at 1 MHz

Table 10. Oscillator Electrical Specifications (Temperature Range = –40 °C to 105 °C Ambient) (continued)

Num	C	Characteristic	Symbol	Min	Typ[1]	Max	Unit
3	D	Feedback resistor • Low range (32 kHz to 100 kHz) • High range (1 MHz to 16 MHz)	R_F	 — —	 10 1	 — —	MΩ
4	D	Series resistor • Low range, low gain (RANGE = 0, HGO = 0) • Low range, high gain (RANGE = 0, HGO = 1)	R_S		 0 100		kΩ
5	D	Series resistor • High range, low gain (RANGE = 1, HGO = 0) • High range, high gain (RANGE = 1, HGO = 1) ≥8 MHz 4 MHz 1 MHz	R_S	 — — —	 0 0 0	 0 10 20	kΩ
6	T	Crystal start-up time[3, 4] • Low range (HGO = 0) • Low range (HGO = 1) • High range (HG0 = 0)[5] • High range (HG0 = 1)[5]	 $t_{CSTL-LP}$ $t_{CSTL-HGO}$ $t_{CSTH-LP}$ $t_{CSTH-HGO}$	 — — — —	 500 3570 4 4	 — — — —	ms
7	D	Square wave input clock frequency (EREFS = 0, ERCLKEN = 1) • FEE or FBE mode[2] • BLPE mode	f_{extal}	 0.03125 0	 — —	 5 40	MHz

1 Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.

2 When ICS is configured for FEE or FBE mode, input clock source must be divisible using RDIV to within the range of 31.25 kHz to 39.0625 kHz.

3 This parameter is characterized and not tested on each device.

4 Proper PC board layout procedures must be followed to achieve specifications.

5 4 MHz crystal

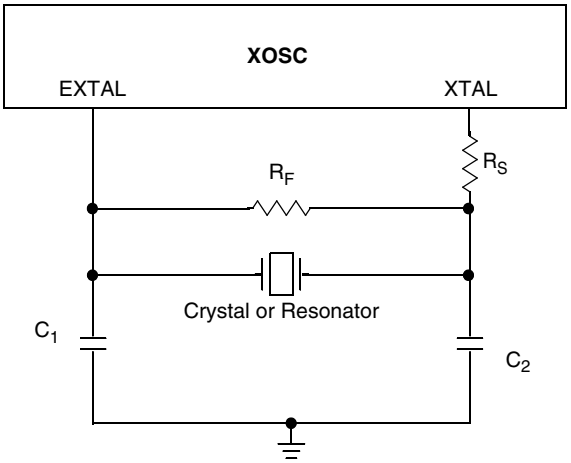


Figure 15. Typical Crystal or Resonator Circuit: High Range and Low Range/High Gain

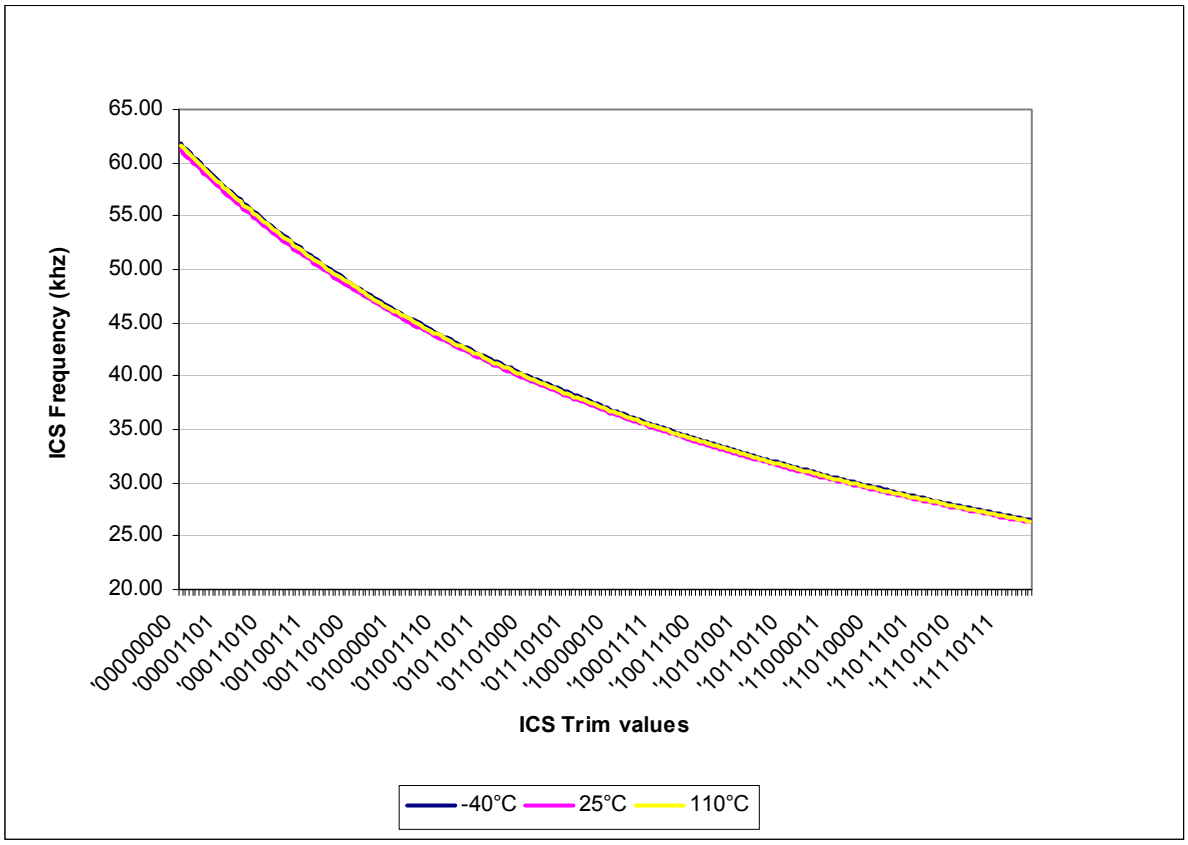


Figure 17. Internal Oscillator Deviation from Trimmed Frequency

2.10 ADC Characteristics

Table 12. 12-bit ADC Operating Conditions

Characteristic	Conditions	Symb	Min	Typ[1]	Max	Unit	Comment
Supply voltage	Absolute	V_{DDAD}	2.7	—	5.5	V	—
	Delta to V_{DD} ($V_{DD} - V_{DDAD}$)[2]	ΔV_{DDAD}	–100	0	+100	mV	—
Ground voltage	Delta to V_{SS} ($V_{SS} - V_{SSAD}$)[2]	ΔV_{SSAD}	–100	0	+100	mV	—
Ref Voltage High	—	V_{REFH}	—	—	—	V	V_{REFH} shorted to V_{DDAD}
Ref Voltage Low	—	V_{REFL}	—	—	—	V	V_{REFL} shorted to V_{SSAD}
Input Voltage	—	V_{ADIN}	V_{REFL}	—	V_{REFH}	V	—
Input Capacitance	—	C_{ADIN}	—	4.5	5.5	pF	—

2.14 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

2.14.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a custom EMC evaluation board while running specialized EMC test software. The radiated emissions from the microcontroller are measured in a TEM cell in two package orientations (North and East).

The maximum radiated RF emissions of the tested configuration in all orientations are less than or equal to the reported emissions levels.

Table 19. Radiated Emissions, Electric Field

Parameter	Symbol	Conditions	Frequency	f_{OSC}/f_{BUS}	Level[1] (Max)	Unit
Radiated emissions, electric field	V_{RE_TEM}	V_{DD} = 5.5 T_A = +25 °C Package type = 80 LQFP	0.15 – 50 MHz	4 MHz crystal 16 MHz bus	10	dBμV
			50 – 150 MHz		14	
			150 – 500 MHz		8	
			500 – 1000 MHz		5	
			IEC Level		L	—
			SAE Level		2	—

1 Data based on qualification test results.

2.14.2 Conducted Transient Susceptibility

Microcontroller transient conducted susceptibility is measured in accordance with an internal Freescale test method. The measurement is performed with the microcontroller installed on a custom EMC evaluation board and running specialized EMC test software designed in compliance with the test method. The conducted susceptibility is determined by injecting the transient susceptibility signal on each pin of the microcontroller. The transient waveform and injection methodology is based on IEC 61000-4-4 (EFT/B). The transient voltage required to cause performance degradation on any pin in the tested configuration is greater than or equal to the reported levels unless otherwise indicated by footnotes below Table 20.

Table 20. Conducted Susceptibility, EFT/B

Parameter	Symbol	Conditions	f_{OSC}/f_{BUS}	Result	Amplitude[1] (Min)	Unit
Conducted susceptibility, electrical fast transient/burst (EFT/B)	V_{CS_EFT}	V_{DD} = 5.5 T_A = +25 °C Package type = 80-pin LQFP	4 kHz crystal 4 MHz bus	A B C D	>4.0[2] >4.0[3] >4.0[4] >4.0	kV

1 Data based on qualification test results. Not tested in production.

2 Exceptions as covered in footnotes 3 and 4.

3 Except pins PHT1, PTH2, PTH3, PTH4, PTH5. See figures below for values.
4 Except pins PTF3, PTH5, PTH4, PHT0, Reset, and BKGD. See figures below for values.

Individual performance of each pin is shown in Figure 27, Figure 28, Figure 29, and Figure 30.

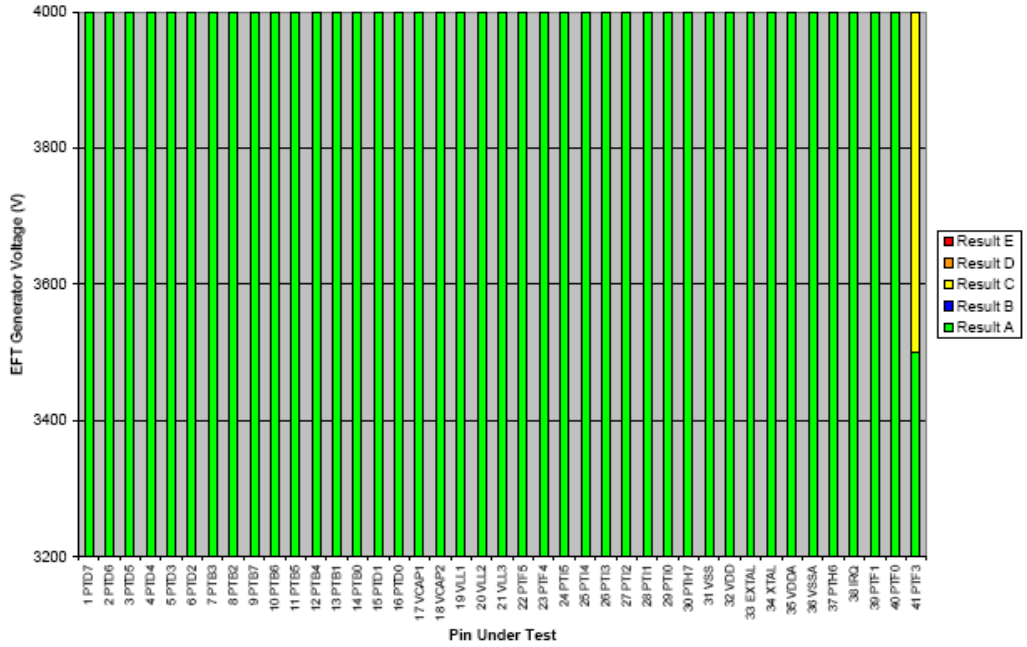
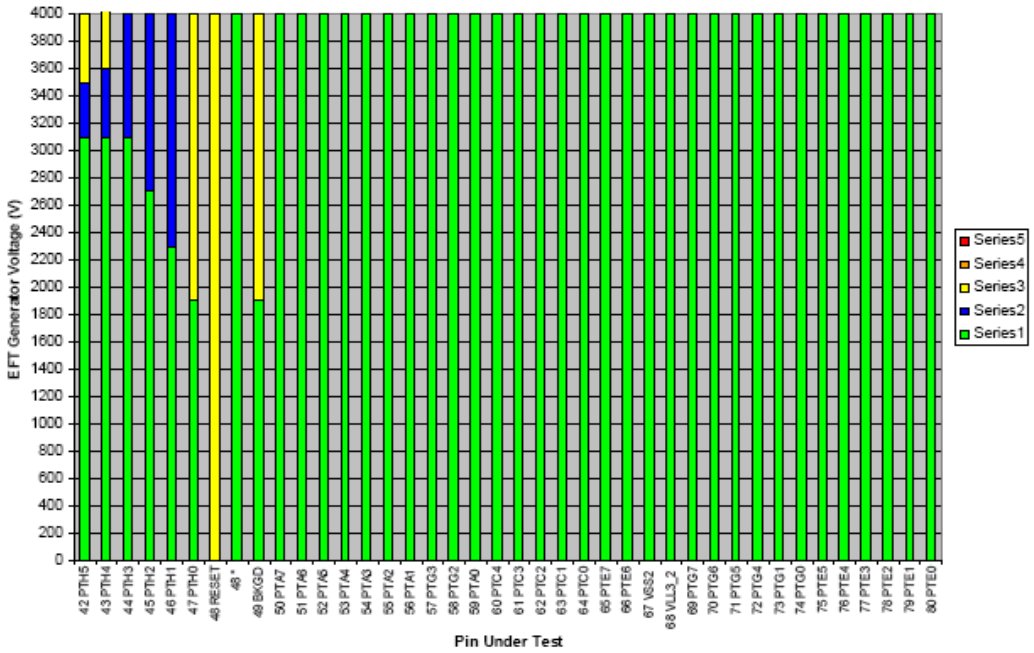


Figure 27. 4 MHz, Positive Polarity Pins 1 – 41



Note:
RESET retested with 0.1 μF capacitor from pin to ground is Class A compliant as shown by 48*.

Figure 28. 4 MHz, Positive Polarity Pins 42 – 80

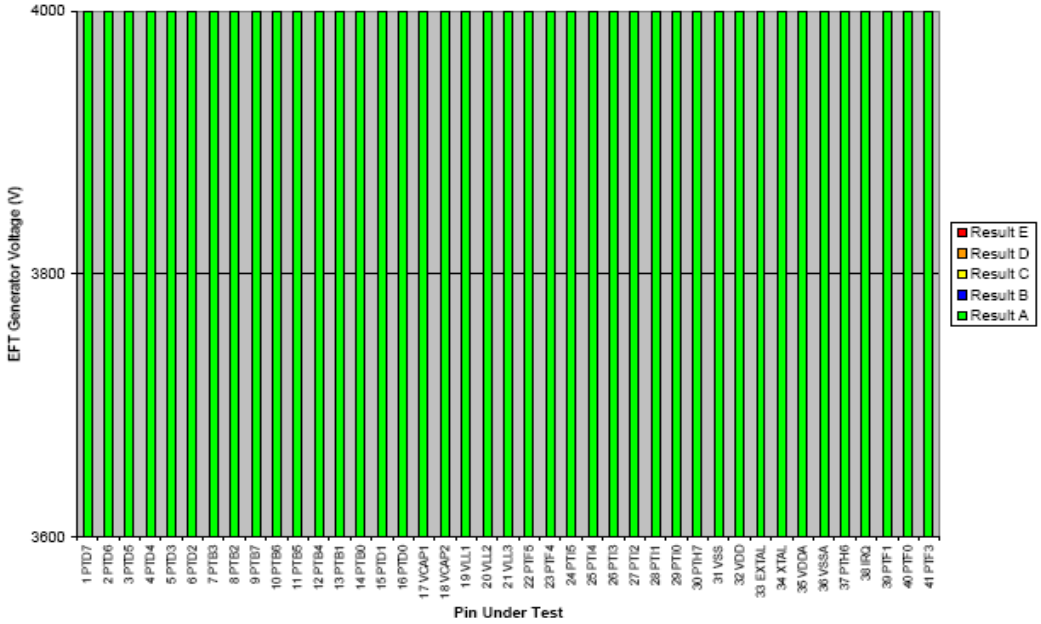
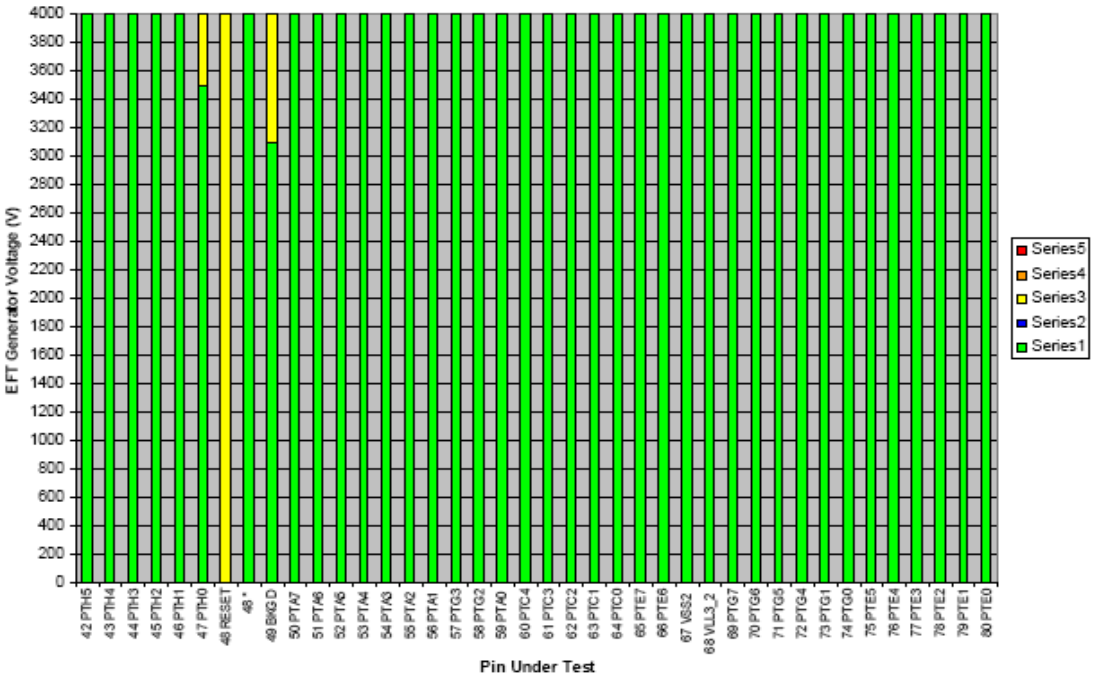


Figure 29. 4 MHz, Negative Polarity Pins 1 – 41



Note:
RESET retested with 0.1 μF capacitor from pin to ground is Class A compliant as shown by 48*.

Figure 30. 4 MHz, Negative Polarity Pins 42 – 80

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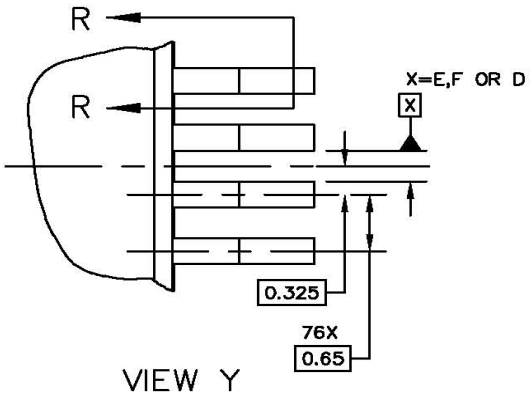
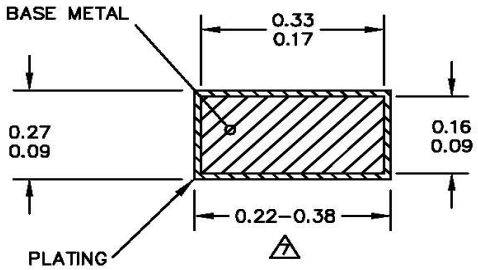
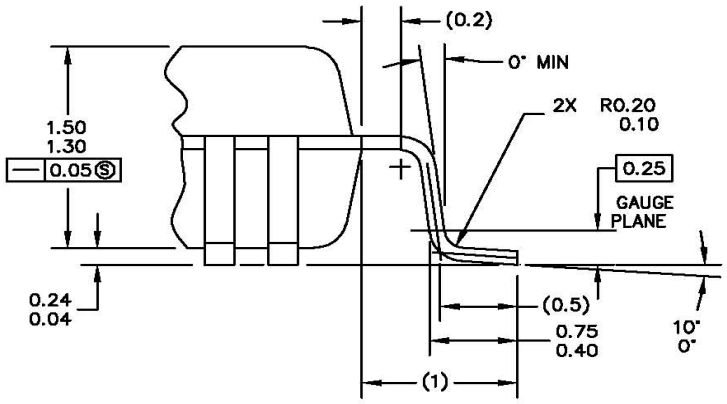


VIEW Y



SECTION R–R
ROTATED 90° CW



VIEW K

TITLE: 80 LD LQFP, 14 X 14 PKG, 0.65 MM PITCH, 1.4 THICK	CASE NUMBER: 917A–03	
	STANDARD: FREESCALE	
	PACKAGE CODE: 8258	SHEET: 2 OF 3

freescale semiconductor	MECHANICAL OUTLINES DICTIONARY	DOCUMENT NO: 98ASS23237W
		PAGE: 917A
	DO NOT SCALE THIS DRAWING	REV: E

NOTES:

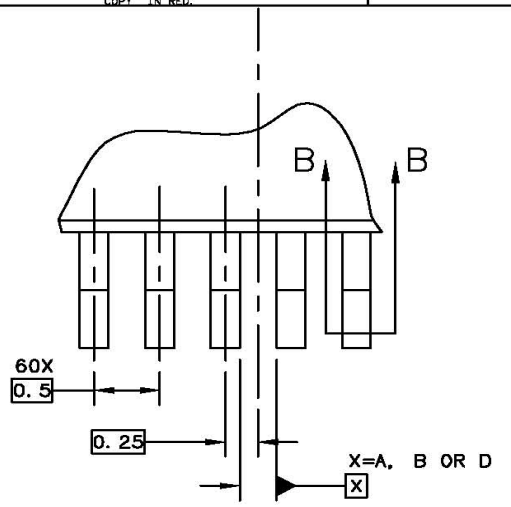
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994.
2. CONTROLLING DIMENSION : MILIMETER.
3. DATUM PLANE H IS LOCATED AT THE BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.
4. DATUM E, F AND D TO BE DETERMINED AT DATUM PLANE H.
5. DIMENSIONS TO BE DETERMINED AT SEATING PLANE C.
6. DIMENSIONS DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 PER SIDE. DIMENSIONS DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H.
7. DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.46. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD OR PROTRUSION 0.07.

TITLE: 80 LD LQFP, 14 X 14 PKG, 0.65 MM PITCH, 1.4 THICK	CASE NUMBER: 917A–03	
	STANDARD: FREESCALE	
	PACKAGE CODE: 8258	SHEET: 3 OF 3

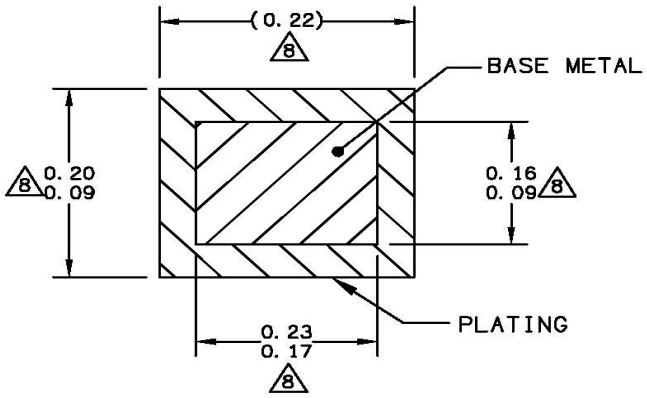
Figure 33. 80-pin LQFP Package Drawing (Case 917A, Doc #98ASS23237W)

freescale semiconductor

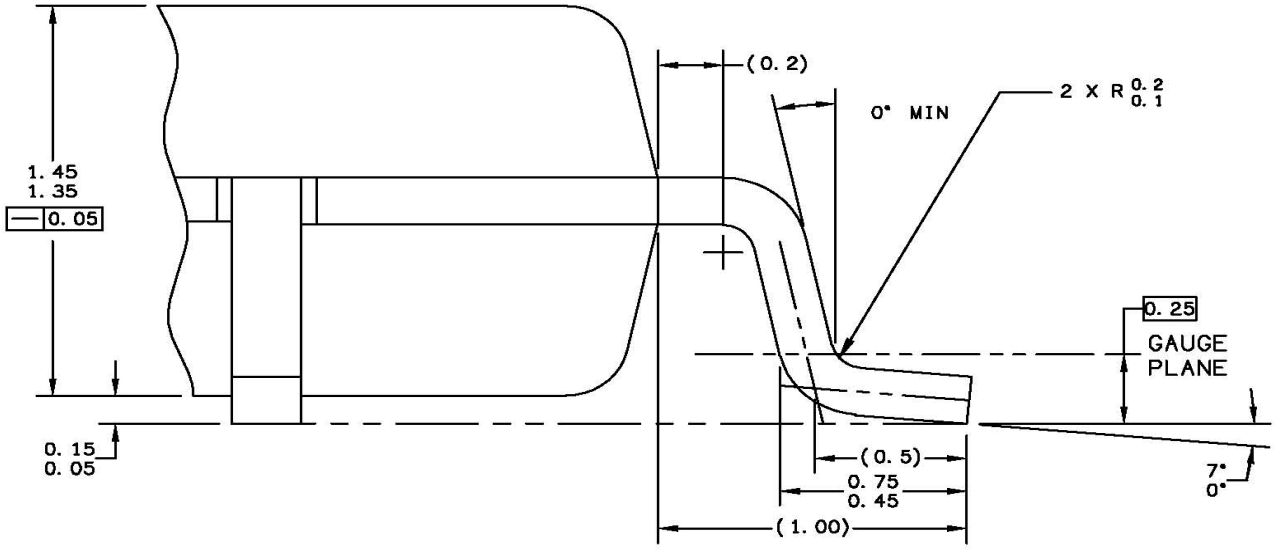
MECHANICAL OUTLINES DICTIONARY	DOCUMENT NO: 98ASS23234W
	PAGE: 840F
DO NOT SCALE THIS DRAWING	REV: E



VIEW Y



SECTION B–B



VIEW AA

TITLE: 64LD LQFP, 10 X 10 X 1.4 PKG, 0.5 PITCH, CASE OUTLINE	CASE NUMBER: 840F–02	
	STANDARD: JEDEC MS–026 BCD	
	PACKAGE CODE: 8426	SHEET: 2 OF 3

freescale semiconductor	MECHANICAL OUTLINES DICTIONARY	DOCUMENT NO: 98ASS23234W
		PAGE: 840F
	DO NOT SCALE THIS DRAWING	REV: E

NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994.
3. DATUMS A, B AND D TO BE DETERMINED AT DATUM PLANE H.
4. DIMENSIONS TO BE DETERMINED AT SEATING PLANE C.
5. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE UPPER LIMIT BY MORE THAN 0.08 mm AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD SHALL NOT BE LESS THAN 0.07 mm.
6. THIS DIMENSION DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 mm PER SIDE. THIS DIMENSION IS MAXIMUM PLASTIC BODY SIZE DIMENSION INCLUDING MOLD MISMATCH.
7. EXACT SHAPE OF EACH CORNER IS OPTIONAL.
8. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.1 mm AND 0.25 mm FROM THE LEAD TIP.

TITLE: 64LD LQFP, 10 X 10 X 1.4 PKG, 0.5 PITCH, CASE OUTLINE	CASE NUMBER: 840F–02	
	STANDARD: JEDEC MS–026 BCD	
	PACKAGE CODE: 8426	SHEET: 3 OF 3

Figure 34. 64-pin LQFP Package Drawing (Case 840F, Doc #98ASS23234W)